





EH39 20 ET T TS -18.432M

Series — RoHS Compliant (Pb-free) 1.8V 4 Pad 3.2mm x 5mm Ceramic SMD LVCMOS Oscillator

Frequency Tolerance/Stability — ±20ppm Maximum

Operating Temperature Range --40°C to +85°C

Nominal Frequency 18.432MHz

Pin 1 Connection
Tri-State (High Impedance)

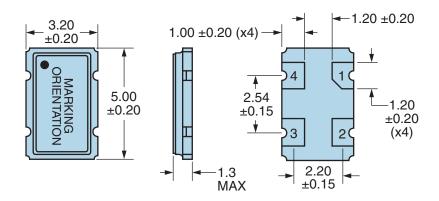
- Duty Cycle 50 ±5(%)

Operating T 260°C Reflorment 260°C Reflo	°C
Operating T 260°C Reflorment 260°C Reflorment 260°C Reflorment 260°C Reflorment 260°C Reflorment 260°C to +8 250°C	emperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, w, Shock, and Vibration) Maximum 9°C
erating Temperature Range -40°C to +88 pply Voltage 1.8Vdc ±5% out Current 3.5mA Maxi tput Voltage Logic High (Voh) 10% of Vdd tput Voltage Logic Low (Vol) 10% of Vdd telfall Time 6nSec Maxi ty Cycle 50 ±5(%) (N ad Drive Capability 15pF Maxim tput Logic Type CMOS 1 Connection Tri-State (H -State Input Voltage (Vih and Vil)	°C
pply Voltage 1.8Vdc ±5% 3.5mA Maxi tput Voltage Logic High (Voh) 10% of Vdd tput Voltage Logic Low (Vol) 10% of Vdd 6nSec Maxi ty Cycle 50 ±5(%) (N 15pF Maxim tput Logic Type CMOS 1 Connection Tri-State (H 90% of Vdd	
trut Current 3.5mA Maxistrut Voltage Logic High (Voh) 4 tput Voltage Logic Low (Vol) 5 te/Fall Time 6 nSec Maxistrut Cycle 6 dd Drive Capability 7 tput Logic Type 7 CMOS 7 Tri-State (H	
tput Voltage Logic High (Voh) tput Voltage Logic Low (Vol) se/Fall Time fnSec Maximaty Cycle ad Drive Capability tput Logic Type 1 Connection Tri-State (H State Input Voltage (Vih and Vil) 90% of Vdd 10% of Vdd 6nSec Maximaty 50 ±5(%) (N 15pF Maximaty CMOS Tri-State (H	
tput Voltage Logic Low (Vol) 10% of Vdd se/Fall Time 6nSec Maxing ty Cycle 50 ±5(%) (No ad Drive Capability 15pF Maxing tput Logic Type CMOS 1 Connection Tri-State (H -State Input Voltage (Vih and Vil) 90% of Vdd	mum (No Load)
ty Cycle ad Drive Capability tput Logic Type Tri-State (H -State Input Voltage (Vih and Vil) 6nSec Maxi 50 ±5(%) (N 15pF Maxim CMOS Tri-State (H	Minimum (IOH = -8mA)
ty Cycle 50 ±5(%) (Mad Drive Capability 15pF Maxim tput Logic Type CMOS 11 Connection Tri-State (Hestate Input Voltage (Vih and Vil) 90% of Vdd	Maximum (IOL = +8mA)
ad Drive Capability tput Logic Type CMOS 1 Connection Tri-State (H State Input Voltage (Vih and Vil) 90% of Vdd	num (Measured at 20% to 80% of waveform)
tput Logic Type CMOS 1 Connection Tri-State (H -State Input Voltage (Vih and Vil) 90% of Vdd	easured at 50% of waveform)
1 Connection Tri-State (H -State Input Voltage (Vih and Vil) 90% of Vdd	um
-State Input Voltage (Vih and Vil) 90% of Vdd	
	gh Impedance)
	Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High
ndby Current 10µA Maxin	um (Pin 1 = Ground)
solute Clock Jitter ±100pSec N	un (i in i = Ground)
art Up Time 10mSec Ma	
orage Temperature Range -55°C to +12	laximum

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)

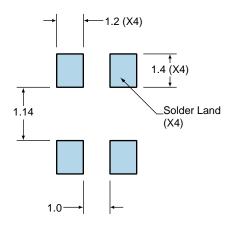


PIN CONNECTION 1 Tri-State 2 Case Ground 3 Output 4 Supply Voltage

LINE	MARKING
1	EPO
	XXXXX XXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

All Dimensions in Millimeters



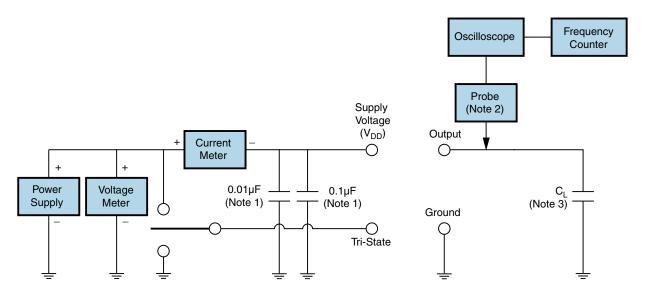
All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value C₁ includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

T _s MAX to T _L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T _L)	217°C
- Time (t _L)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.